# SANYO

## 2SB1202/2SD1802

# **High-Current Switching Applications**

## **Applications**

· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

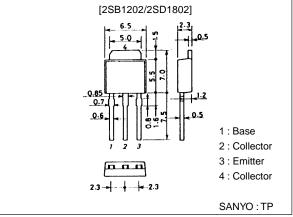
## **Features**

- · Adoption of FBET, MBIT processes.
- · Large currrent capacity and wide ASO.
- · Low collector-to-emitter saturation voltage.
- · Fast switching speed.
- · Small and slim package making it easy to make 2SB1202/2SD1802-used sets smaller.

## **Package Dimensions**

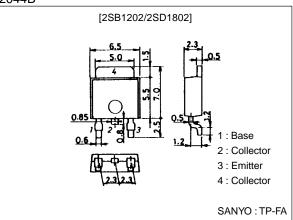
unit:mm

#### 2045B



unit:mm

#### 2044B



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():2SB1202

## **Specifications**

## Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)50	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(–)6	V
Collector Current	lc		(–)3	Α
Collector Current (Pulse)	l <sub>CP</sub>		(–)6	Α
Collector Dissipation	PC		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

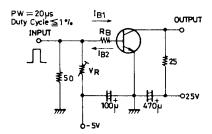
## Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(-)1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA	100*		560*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)3A	35			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		150		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		(39)25		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)100mA		0.19	0.5	V
				(-0.35)	(-0.7)	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)100mA		(-)0.94	(-)1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0	(-)60			V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)10μΑ, I <sub>C</sub> =0	(-)6			V
Turn-ON Time	ton	See specified Test Circuit		70		ns
Storage Time	t <sub>stg</sub>	See specified Test Circuit		(450)		ns
				650		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		35		ns

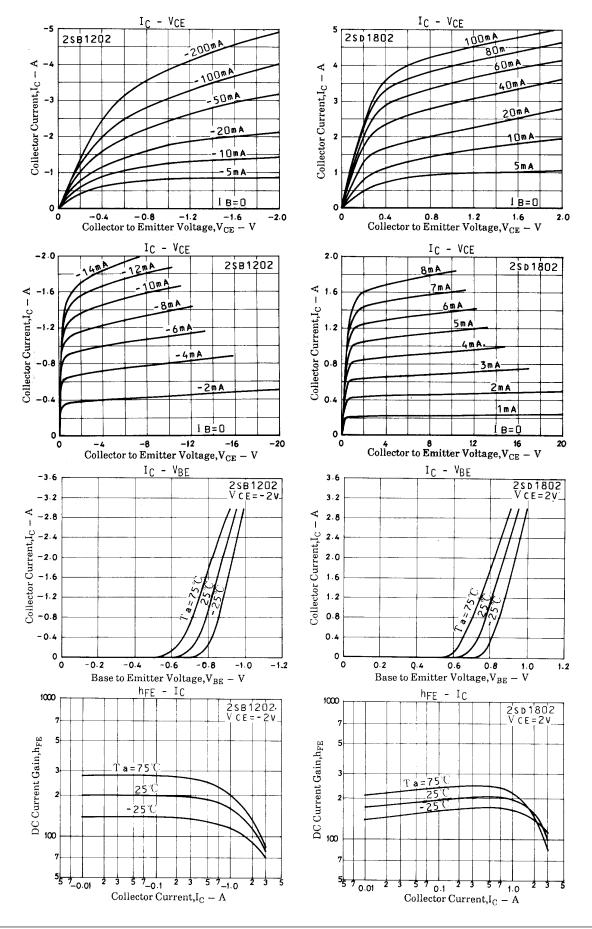
 $<sup>\</sup>ast$  : The 2SB1202/2SD1802 are classified by 100mA  $h_{FE}$  as follows :

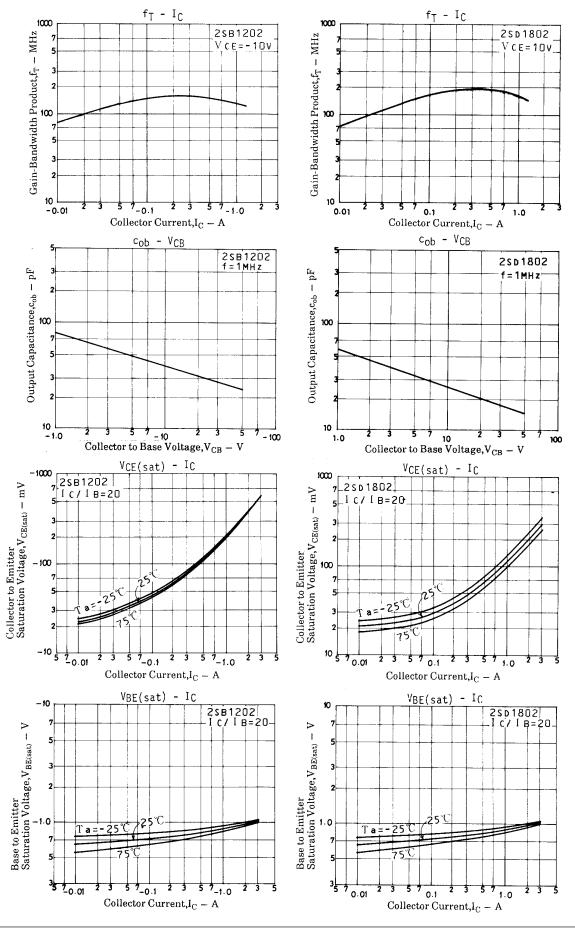
100 R 200 140 S 280	200 T 400	280 U 560
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## **Switching Time Test Circuit**

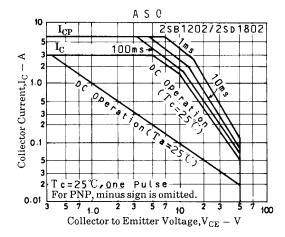


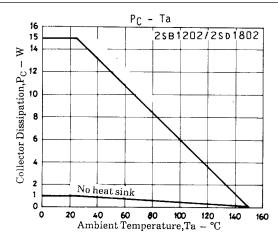
I C=10 I B1=-10 I B2=1A (For PNP, the polarity is reversed.) Unit (resistance: Ω, capacitance: F)





#### 2SB1202/2SD1802





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